

N-channel 800 V, 0.80 Ω typ., 4.5 A Zener-protected SuperMESH™ 5 Power MOSFET in a PowerFLAT™ 5x6 VHV package

Datasheet – production data

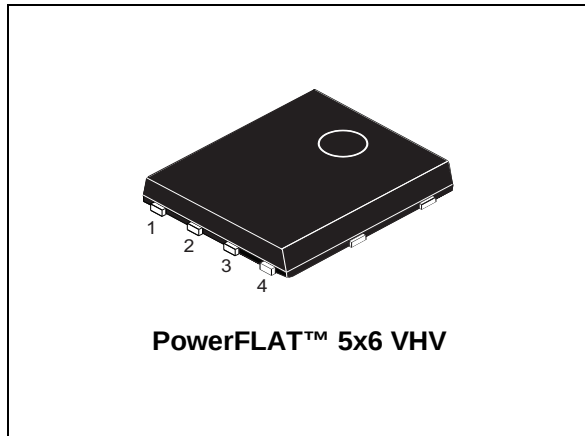
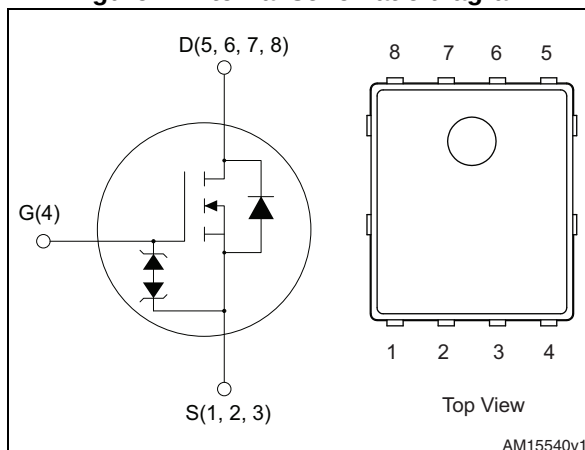


Figure 1. Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)max.}$	I_D
STL8N80K5	800 V	0.95 Ω	4.5 A

- Outstanding $R_{DS(on)}$ *area
- Worldwide best FOM (figure of merit)
- Ultra low gate charge
- 100% avalanche tested
- Zener protected

Applications

- Switching applications

Description

This N-channel Zener-protected Power MOSFET is designed using ST's revolutionary avalanche-rugged very high voltage SuperMESH™ 5 technology, based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance, and ultra-low gate charge for applications which require superior power density and high efficiency.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL8N80K5	8N80K5	PowerFLAT™ 5x6 VHV	Tape and reel

Contents

1 **Electrical ratings** **3**

2 **Electrical characteristics** **4**

 2.1 Electrical characteristics (curves) 6

3 **Test circuits** **9**

4 **Package mechanical data** **10**

5 **Packaging mechanical data** **14**

6 **Revision history** **16**



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	4.5	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3	A
$I_{DM}^{(1),(2)}$	Drain current (pulsed)	18	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	42	W
$I_{AR}^{(3)}$	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	2	A
$E_{AS}^{(4)}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	114	mJ
$dv/dt^{(5)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(6)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature		$^\circ\text{C}$

1. The value is rated according to $R_{thj-case}$ and limited by package.
2. Pulse width limited by safe operating area.
3. Pulse width limited by T_{jmax}
4. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$
5. $I_{SD} \leq 4.5\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DS(peak)} \leq V_{(BR)DSS}$
6. $V_{DS} \leq 640\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	3	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	59	$^\circ\text{C}/\text{W}$

1. When mounted on 1inch² FR-4 board, 2 oz Cu.

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 800\text{ V}$			1	μA
		$V_{DS} = 800\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}$			50	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$		0.80	0.95	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	450	-	pF
C_{oss}	Output capacitance		-	50	-	pF
C_{rss}	Reverse transfer capacitance		-	1	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }640\text{ V}$, $V_{GS} = 0$	-	57	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	24	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0$	-	6	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}$, $I_D = 6\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 16)	-	16.5	-	nC
Q_{gs}	Gate-source charge		-	3.2	-	nC
Q_{gd}	Gate-drain charge		-	11	-	nC

1. $C_{oss\text{ eq}}$ time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. $C_{oss\text{ eq}}$ energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 3\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15), (see Figure 20)	-	12	-	ns
t_r	Rise time		-	14	-	ns
$t_{d(off)}$	Turn-off delay time		-	32	-	ns
t_f	Fall time		-	20	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		4.5	A
I_{SDM}	Source-drain current (pulsed)		-		18	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 6\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 17)	-	300		ns
Q_{rr}	Reverse recovery charge		-	3		μC
I_{RRM}	Reverse recovery current		-	20		A
t_{rr}	Reverse recovery time	$I_{SD} = 6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	415		ns
Q_{rr}	Reverse recovery charge		-	3.8		μC
I_{RRM}	Reverse recovery current		-	18		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0$	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance not only the device's ESD capability, but also to make them capable of safely absorbing any voltage transients that may occasionally be applied from gate to source. In this respect, the Zener voltage is appropriate to achieve efficient and cost-effective protection of device integrity. The integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

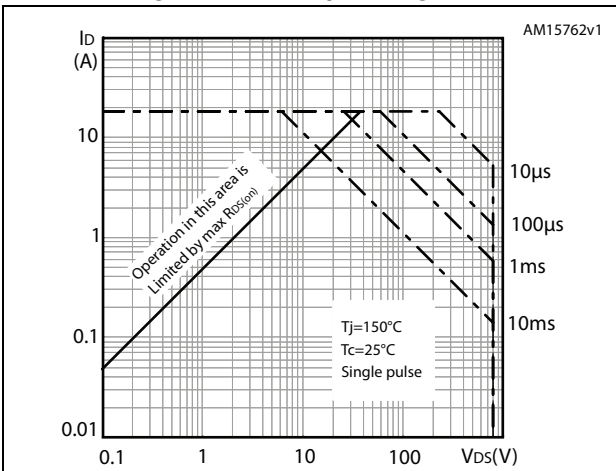


Figure 3. Thermal impedance

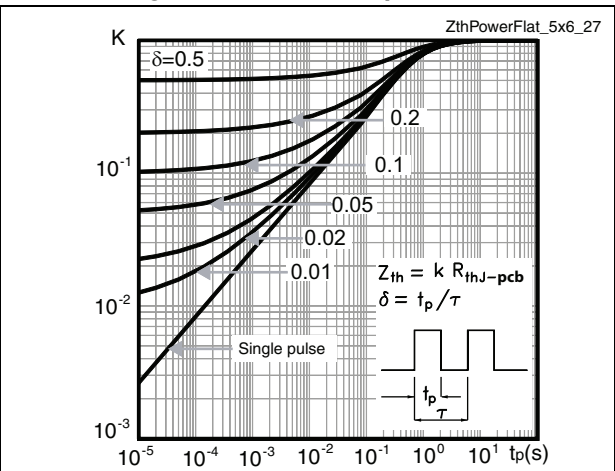


Figure 4. Output characteristics

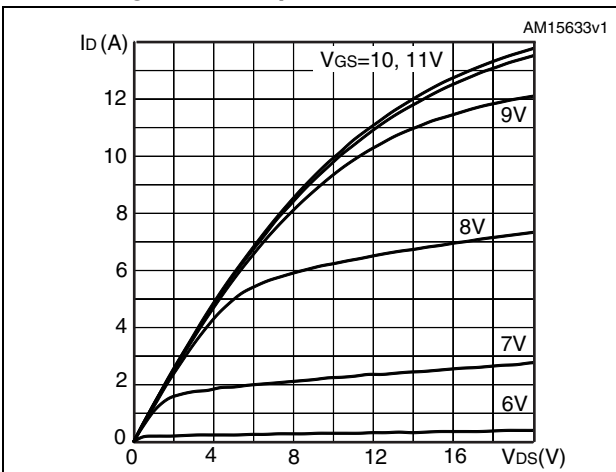


Figure 5. Transfer characteristics

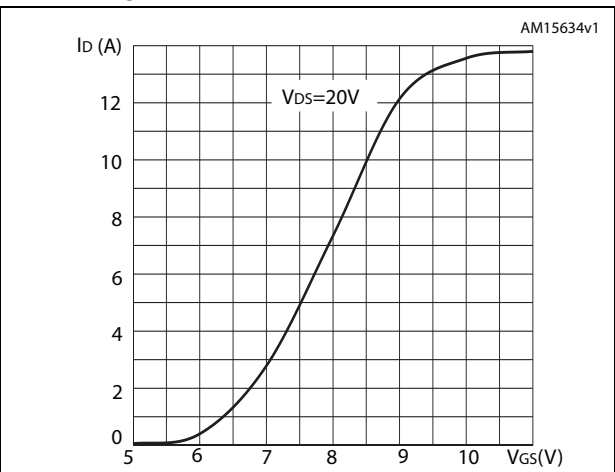


Figure 6. Gate charge vs gate-source voltage

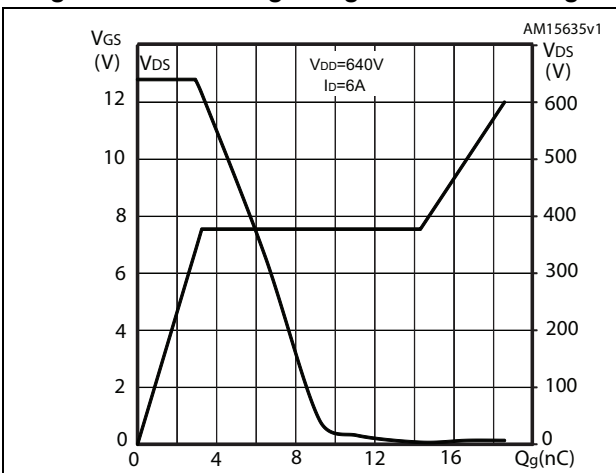


Figure 7. Static drain-source on-resistance

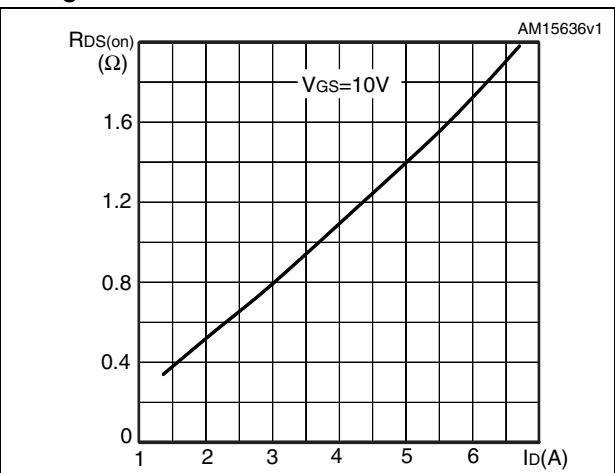


Figure 8. Capacitance variations

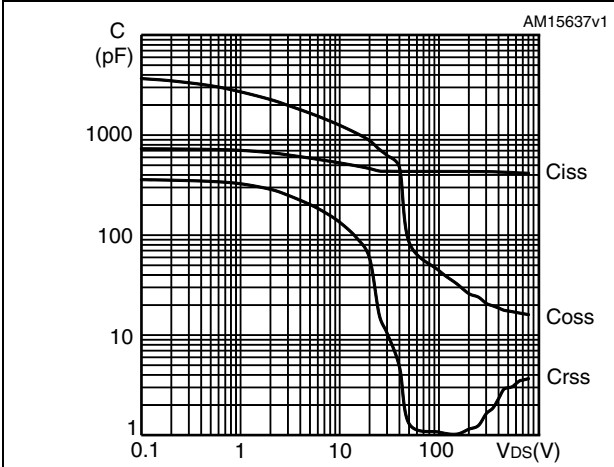


Figure 9. Output capacitance stored energy

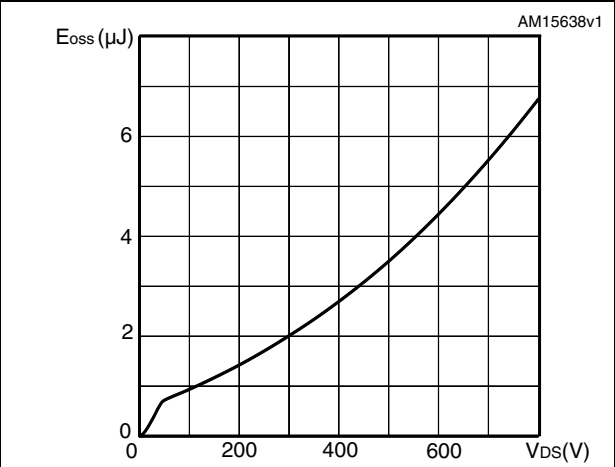


Figure 10. Normalized gate threshold voltage vs. temperature

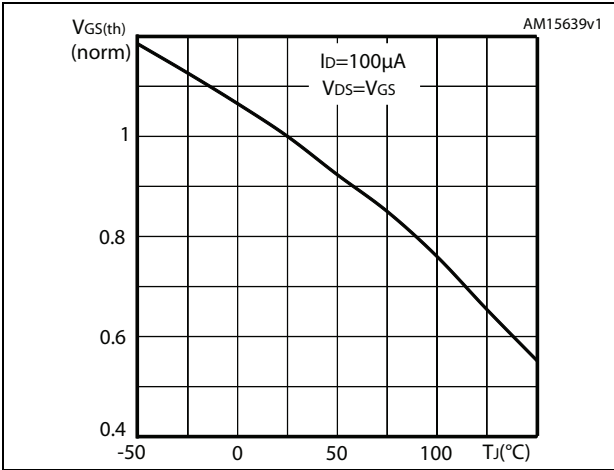


Figure 11. Normalized on-resistance vs. temperature

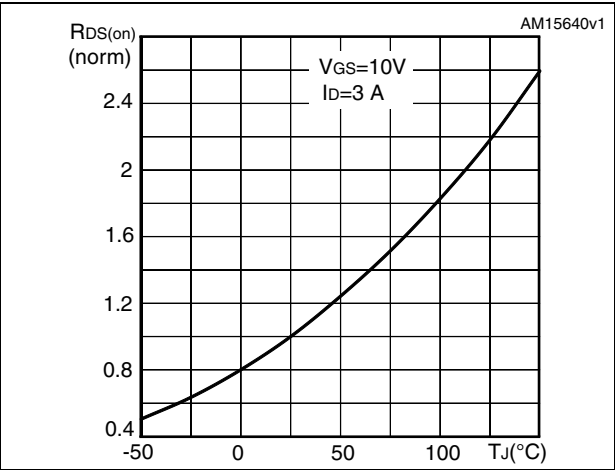


Figure 12. Drain-source diode forward characteristics

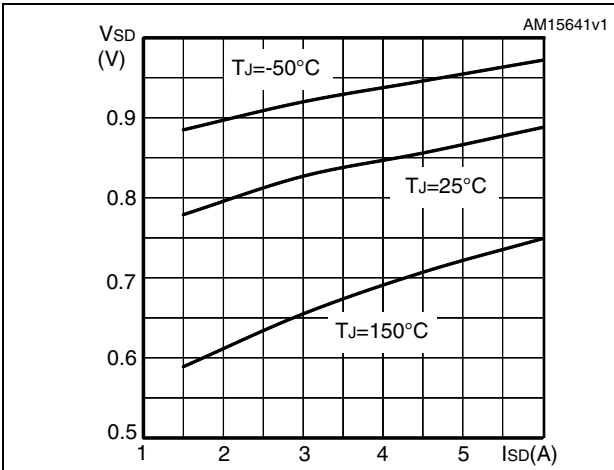


Figure 13. Normalized V_{DS} vs. temperature

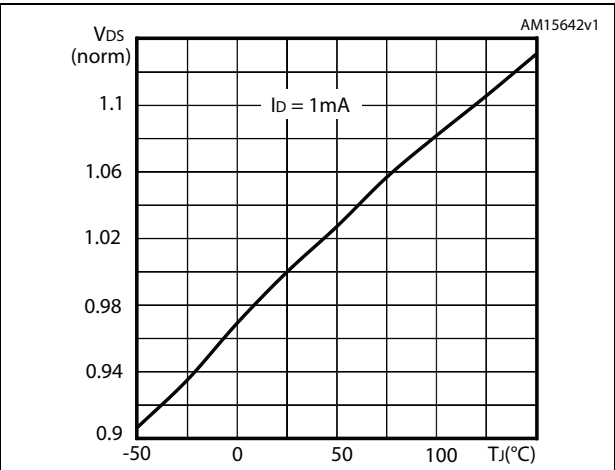
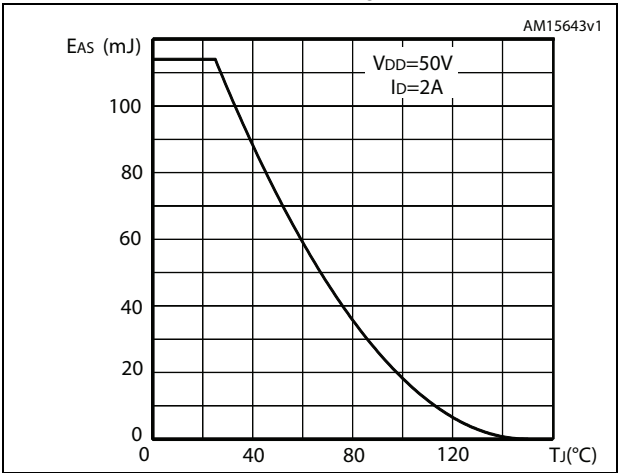


Figure 14. Maximum avalanche energy vs.
starting T_J



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 9. PowerFLAT™ 5x6 VHV mechanical data

DIM	mm.		
	min.	typ.	max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
E	5.95	6.15	6.35
D2	4.30	4.40	4.50
E2	2.40	2.50	2.60
e		1.27	
L	0.50	0.55	0.60
K	2.60	2.70	2.80
aaa		0.15	
bbb		0.15	
ccc		0.10	
eee		0.10	

Figure 21. PowerFLAT™ 5x6 VHV

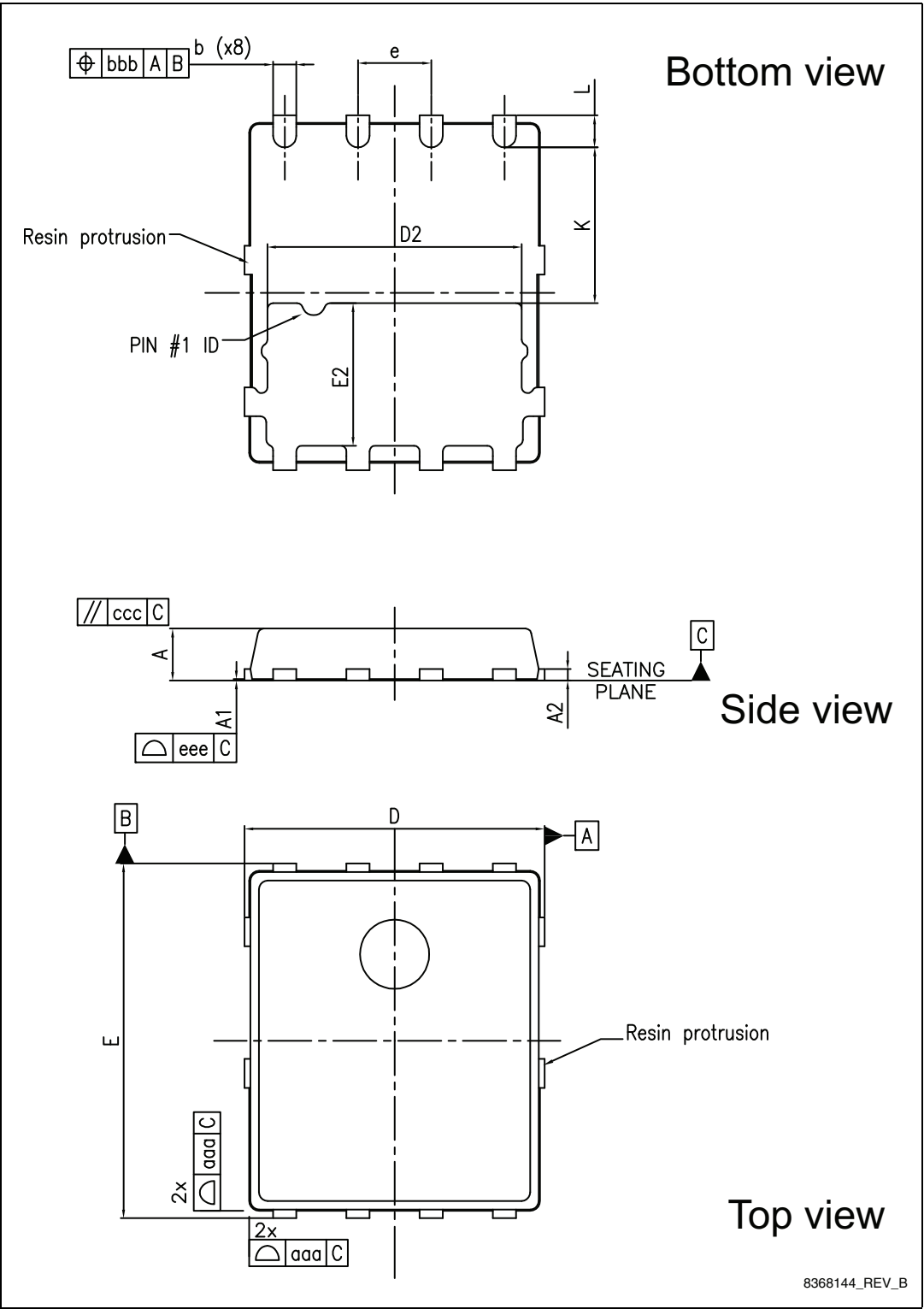
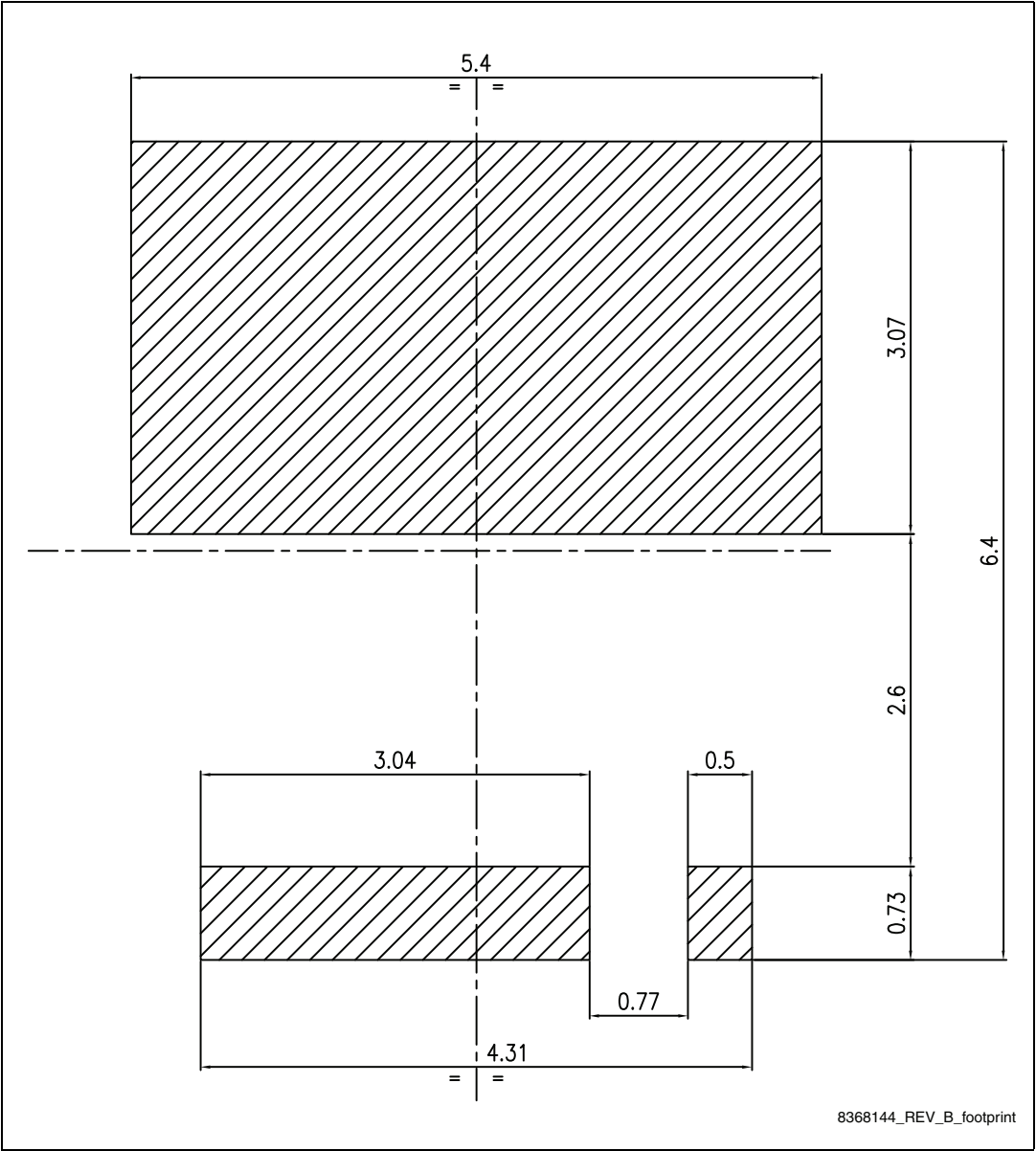


Figure 22. PowerFLAT™ 5x6 VHV (dimensions are in mm)



5 Packaging mechanical data

Figure 23. PowerFLAT™ 5x6 tape

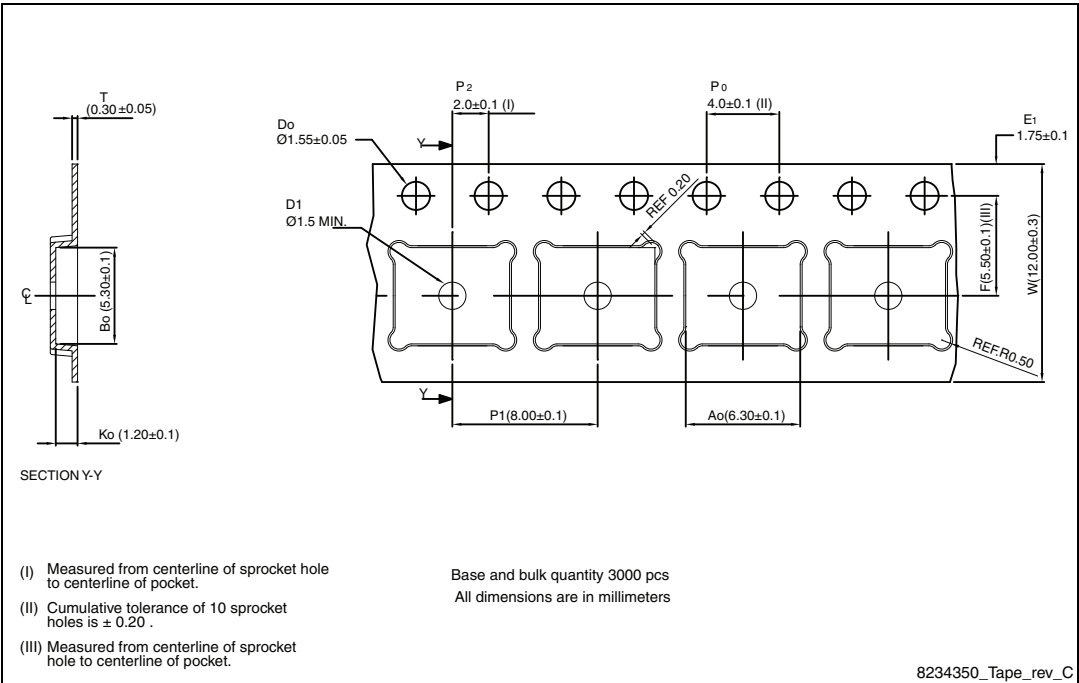


Figure 24. PowerFLAT™ 5x6 package orientation in carrier tape.

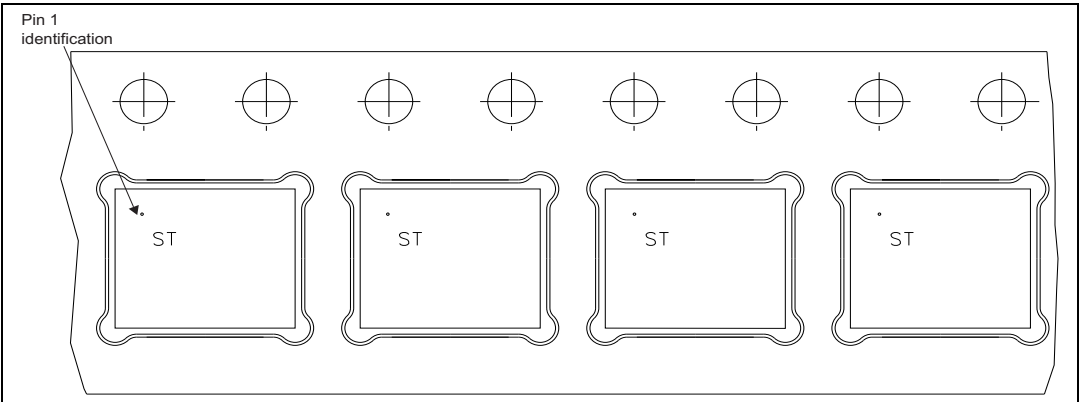
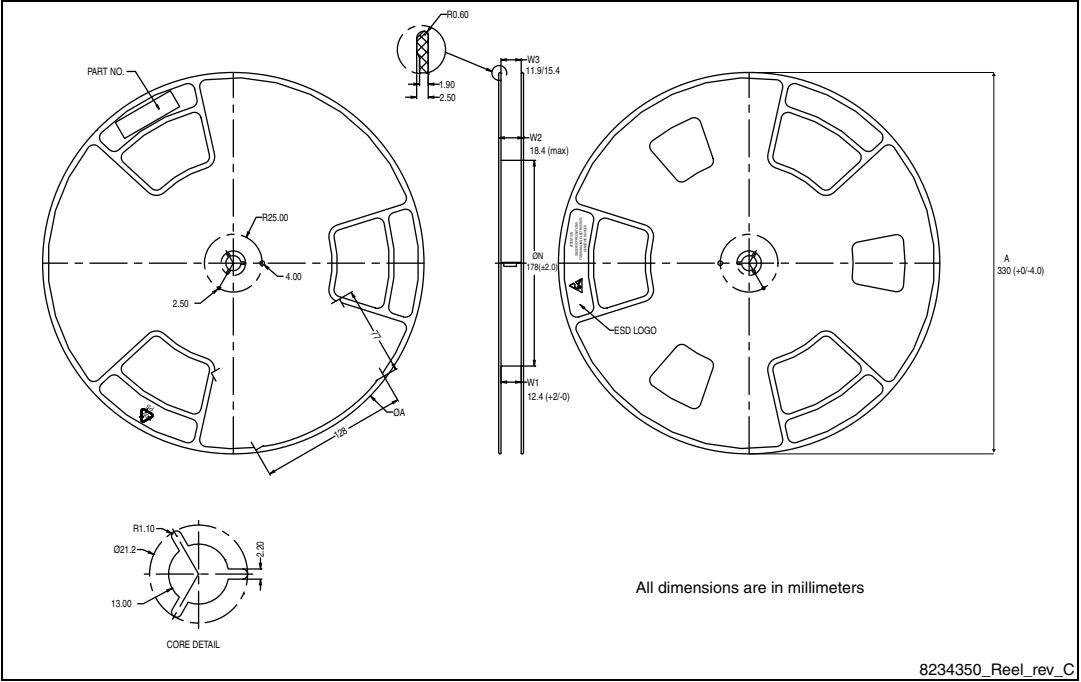


Figure 25. PowerFLAT™ 5x6 reel



6 Revision history

Table 10. Document revision history

Date	Revision	Changes
18-Dec-2012	1	First release.
22-Apr-2013	2	– Deleted: V_{DS}, drain current (continuous) at $T_{amb} = 25\text{ °C}$ and $T_{amb} = 100\text{ °C}$, total dissipation at $T_{amb} = 25\text{ °C}$ in Table 2 – Modified: P_{TOT}, I_{AR} and E_{AS} values in Table 2 – Added: MOSFET dv/dt ruggedness parameter and note 6 in Table 2 – Modified: values in Table 3, $R_{DS(on)}$ typ in Table 4, the entire typical values in Table 5, 6 and 7 – Inserted: Section 2.1: Electrical characteristics (curves)
19-Nov-2013	3	– Modified: Figure 3, 15, 16, 17 and 18 – Minor text changes

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